

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	4803	((438/149) or (438/311) or (438/459) or (438/584) or (438/758) or (438/795) or (438/909) or (438/935)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/06 11:03
L2	0	1 and ((sic or (silicon adj carbide)) same ((cvd or chemical adj vapor adj deposition) same (no near2 sinter\$3)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 12:16
L3	7	((sic or (silicon adj carbide)) same ((cvd or chemical adj vapor adj deposition) same (no near2 sinter\$3)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 11:11
L4	129	boat same (sic or (silicon adj carbide)) same (cvd or (chemical adj vapor adj deposition) )	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 12:15
L5	1	4 and (no near2 sinter\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 11:13
L6	318	1 and (tft or (thin near2 film)) same (soi or (silicon adj on adj insulator\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 12:19
S1	34	silicon adj boat	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/30 22:22
S2	34	silicon adj boat	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/11/20 11:08

S3	60174	silicon adj carbide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/11/20 18:18
S4	92082	cvd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/11/20 18:18
S5	2120	(silicon adj carbide) same cvd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/11/20 18:18
S6	66246	boat	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/11/20 18:18
S7	41	((silicon adj carbide) same cvd) same boat	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/11/20 18:18
S8	34	silicon adj boat	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/11/21 19:44
S9	1	((silicon adj carbide) same cvd) same boat) and (silicon adj boat)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/11/20 18:43
S10	74	((silicon adj carbide) same cvd) same boat) or (silicon adj boat)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/11/20 18:43
S11	14400	soi	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/11/21 19:43
S12	34	silicon adj boat	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/11/21 19:44

S13	1	soi same (silicon adj boat)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/11/21 19:46
S14	1146922	semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/11/21 19:50
S15	5	(silicon adj boat) same semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/11/21 19:46
S16	12	semiconductor adj on adj insulat\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/11/07 18:28
S17	14562	soi	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/12/02 11:04
S18	508529	transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/12/02 11:04
S19	3801	soi same transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/12/02 11:04
S20	60532	silicon adj carbide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/12/02 11:04
S21	10	(soi same transistor) same (silicon adj carbide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/11/07 18:28
S22	15468	soi or (silicon near2 insulator)	US-PGPUB; USPAT	OR	ON	2003/05/18 20:25
S23	265	silicon near2 boat	US-PGPUB; USPAT	OR	ON	2003/05/18 20:25
S24	14	(soi or (silicon near2 insulator)) and (silicon near2 boat)	US-PGPUB; USPAT	OR	ON	2003/05/18 20:26

S25	13	((soi or (silicon near2 insulator)) and (silicon near2 boat)) and @ad<"20020307"	US-PGPUB; USPAT	OR	ON	2003/05/18 20:27
S26	1	("6468884").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2003/10/29 10:53
S27	4619	((438/149) or (438/311) or (438/459) or (438/584) or (438/706) or (438/758) or (438/795) or (438/909) or (438/935)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/04/18 20:21
S28	405	(silicon or ((single near2 crystal) adj silicon) or (poly near2 silicon) or (silicon near2 carbide)) near2 boat	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/07 14:33
S29	20	((((438/149) or (438/311) or (438/459) or (438/584) or (438/706) or (438/758) or (438/795) or (438/909) or (438/935)).CCLS.) and ((silicon or ((single near2 crystal) adj silicon) or (poly near2 silicon) or (silicon near2 carbide)) near2 boat)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/07 14:26
S30	100	(silicon near2 carbide) near2 boat	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/07 18:29
S31	8	((((438/149) or (438/311) or (438/459) or (438/584) or (438/706) or (438/758) or (438/795) or (438/909) or (438/935)).CCLS.) and ((silicon near2 carbide) near2 boat)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/07 14:33
S32	0	"6296709".URPN.	USPAT	OR	OFF	2003/11/07 14:37
S33	5	("4640223"   "4964378"   "5001327"   "5029554"   "6139642").PN.	USPAT	OR	OFF	2003/11/07 14:37
S34	7513	(soi or(semiconductor adj on adj insulat\$3)) near2 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/07 18:29
S35	100	(silicon near2 carbide) near2 boat	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/07 18:30

S36	2	((soi or(semiconductor adj on adj insulat\$3)) near2 substrate) same ((silicon near2 carbide) near2 boat)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/07 18:30
S37	5041	((438/149) or (438/311) or (438/459) or (438/584) or (438/706) or (438/758) or (438/795) or (438/909) or (438/935)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/30 22:21
S38	37845	(hold or holding) near portion	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/18 20:22
S39	20782	SOI or (silicon adj on adj insulator)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/18 20:23
S40	23846	reducing near atmosphere	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/18 20:23
S41	805976	hydrogen	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/18 20:23
S42	2	((hold or holding) near portion) same (SOI or (silicon adj on adj insulator))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/18 20:24
S43	96	((hold or holding) near portion) and (SOI or (silicon adj on adj insulator))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/18 20:24
S44	1	((((hold or holding) near portion) and (SOI or (silicon adj on adj insulator))) and (reducing near atmosphere))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/18 20:24
S45	1	(((((hold or holding) near portion) and (SOI or (silicon adj on adj insulator))) and (reducing near atmosphere)) and hydrogen	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/18 20:24

S46	5645	((438/149) or (438/311) or (438/459) or (438/584) or (438/706) or (438/758) or (438/795) or (438/909) or (438/935)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/30 22:21
S47	408	silicon near2 boat	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/30 22:22
S48	21	((((438/149) or (438/311) or (438/459) or (438/584) or (438/706) or (438/758) or (438/795) or (438/909) or (438/935)).CCLS.) and (silicon near2 boat)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/30 22:26
S49	16	(((((438/149) or (438/311) or (438/459) or (438/584) or (438/706) or (438/758) or (438/795) or (438/909) or (438/935)).CCLS.) and (silicon near2 boat)) and hydrogen	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/30 22:30
S50	1	(((((438/149) or (438/311) or (438/459) or (438/584) or (438/706) or (438/758) or (438/795) or (438/909) or (438/935)).CCLS.) and (silicon near2 boat)) and hydrogen) and (hold\$3 near2 portion)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/30 22:30
S51	1	("5378912").PN.	USPAT; USOCR	OR	OFF	2004/10/30 22:32
S52	14821	soi or (silicon near2 insulator)	US-PGPUB; USPAT	OR	OFF	2003/05/18 20:25
S53	2275	((438/149) or (438/311) or (438/584) or (438/758) or (438/909) or (438/935)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/11/07 14:15
S54	3354	((438/149) or (438/311) or (438/459) or (438/584) or (438/758) or (438/795) or (438/909) or (438/935)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/06 11:01